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Kind regards,

Team Nexperia

74HC75

Quad bistable transparant latch

Rev. 4 — 24 February 2016 Product data sheet

1. General description

The 74HC75 is a quad bistable transparent latch with complementary outputs. Two latches are simultaneously controlled by one of two active HIGH enable inputs (LE12 and LE34). When LEnn is HIGH, the data enters the latches and appears at the nQ outputs. The nQ outputs follow the data inputs (nD) as long as LEnn is HIGH (transparent). The data on the nD inputs one set-up time prior to the HIGH-to-LOW transition of the LEnn will be stored in the latches. The latched outputs remain stable as long as the LEnn is LOW. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Complementary Q and $\overline{Q}$ outputs
- V_{CC} and GND on the center pins
- Low-power dissipation
- Complies with JEDEC standard no. 7A
- Input levels:
  - For 74HC75: CMOS level
- ESD protection:
  - HBM EIA/JESD22-A114F exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +80 °C and from –40 °C to +125 °C.

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC75D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC75DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HC75PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

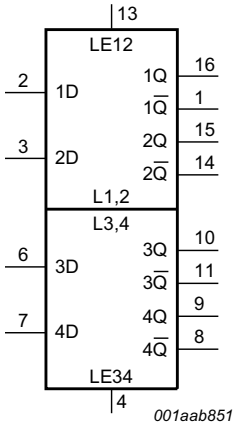

Fig 1. Logic symbol

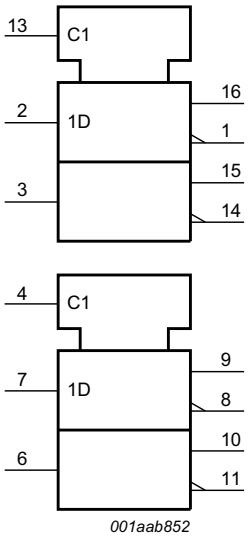

Fig 2. IEC logic symbol

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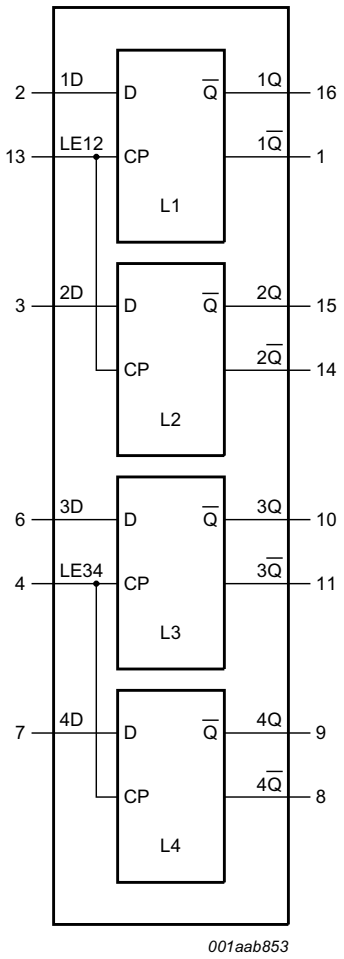

Fig 3. Functional diagram

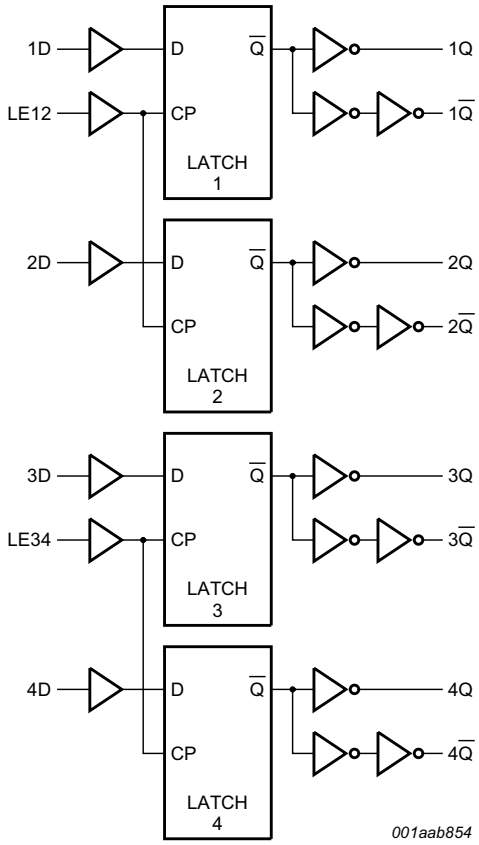

Fig 4. Logic diagram

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5. Pinning information

5.1 Pinning

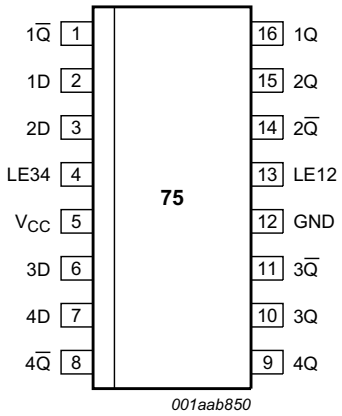

Fig 5. Pin configuration SO16, SSOP16 and TSSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1$\overline{Q}$, 2$\overline{Q}$, 3$\overline{Q}$, 4$\overline{Q}$	1, 14, 11, 8	complementary latch output
1D, 2D, 3D, 4D	2, 3, 6, 7	data input
LE34	4	latch enable input for latches 3 and 4 (active HIGH)
V_{CC}	5	positive supply voltage
GND	12	ground (0 V)
LE12	13	latch enable input for latches 1 and 2 (active HIGH)
1Q, 2Q, 3Q, 4Q	16, 15, 10, 9	latch output

6. Functional description

6.1 Function table

Table 3. Function table[1]

Operating mode	Input		Output	
	LEnn	nD	nQ	n$\overline{Q}$
Data enabled	H	L	L	H
	H	H	H	L
Data latched	L	X	q	$\overline{q}$

[1] H = HIGH voltage level;
L = LOW voltage level;
q = lower case letters indicate the state of the referenced output one set-up time prior to the HIGH-to-LOW LEnn transition;
X = don't care.

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_{OK}	output clamping current	$V_O < –0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	$V_O = –0.5$ V to $V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			–50	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = –40$ °C to +125 °C				
		SO16 package	[2]	-	500	mW
		(T)SSOP16 package	[3]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0$ V	-	-	625	ns/V
		$V_{CC} = 4.5$ V	-	1.67	139	ns/V
		$V_{CC} = 6.0$ V	-	-	83	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = 25$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0$ V	1.5	1.2	-	V
		$V_{CC} = 4.5$ V	3.15	2.4	-	V
		$V_{CC} = 6.0$ V	4.2	3.2	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0$ V	-	0.8	0.5	V
		$V_{CC} = 4.5$ V	-	2.1	1.35	V
		$V_{CC} = 6.0$ V	-	2.8	1.8	V

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Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μA; $V_{CC} = 2.0$ V	1.9	2.0	-	V
		$I_O = -20$ μA; $V_{CC} = 4.5$ V	4.4	4.5	-	V
		$I_O = -20$ μA; $V_{CC} = 6.0$ V	5.9	6.0	-	V
		$I_O = -4$ mA; $V_{CC} = 4.5$ V	3.98	4.32	-	V
		$I_O = -5.2$ mA; $V_{CC} = 6.0$ V	5.48	5.81	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μA; $V_{CC} = 2.0$ V	-	0	0.1	V
		$I_O = 20$ μA; $V_{CC} = 4.5$ V	-	0	0.1	V
		$I_O = 20$ μA; $V_{CC} = 6.0$ V	-	0	0.1	V
		$I_O = 4$ mA; $V_{CC} = 4.5$ V	-	0.15	0.26	V
		$I_O = 5.2$ mA; $V_{CC} = 6.0$ V	-	0.16	0.26	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±0.1	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	μA
C_I	input capacitance		-	3.5	-	pF
$T_{amb} = -40$ °C to +85 °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0$ V	1.5	-	-	V
		$V_{CC} = 4.5$ V	3.15	-	-	V
		$V_{CC} = 6.0$ V	4.2	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0$ V	-	-	0.5	V
		$V_{CC} = 4.5$ V	-	-	1.35	V
		$V_{CC} = 6.0$ V	-	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μA; $V_{CC} = 2.0$ V	1.9	-	-	V
		$I_O = -20$ μA; $V_{CC} = 4.5$ V	4.4	-	-	V
		$I_O = -20$ μA; $V_{CC} = 6.0$ V	5.9	-	-	V
		$I_O = -4$ mA; $V_{CC} = 4.5$ V	3.84	-	-	V
		$I_O = -5.2$ mA; $V_{CC} = 6.0$ V	5.34	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μA; $V_{CC} = 2.0$ V	-	-	0.1	V
		$I_O = 20$ μA; $V_{CC} = 4.5$ V	-	-	0.1	V
		$I_O = 20$ μA; $V_{CC} = 6.0$ V	-	-	0.1	V
		$I_O = 4$ mA; $V_{CC} = 4.5$ V	-	-	0.33	V
		$I_O = 5.2$ mA; $V_{CC} = 6.0$ V	-	-	0.33	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±1.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	80	μA

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Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = –40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	V
		V_{CC} = 4.5 V	3.15	-	-	V
		V_{CC} = 6.0 V	4.2	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	V
		V_{CC} = 4.5 V	-	-	1.35	V
		V_{CC} = 6.0 V	-	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}		-		
		I_O = –20 μA; V_{CC} = 2.0 V	1.9	-	-	V
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	-	-	V
		I_O = –20 μA; V_{CC} = 6.0 V	5.9	-	-	V
		I_O = –4 mA; V_{CC} = 4.5 V	3.7	-	-	V
		I_O = –5.2 mA; V_{CC} = 6.0 V	5.2	-	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}		-		
		I_O = 20 μA; V_{CC} = 2.0 V	-	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 4.5 V	-	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	160	μA

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10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF; unless otherwise specified, see Figure 10.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
t_{PHL}, t_{PLH}	propagation delay nD to nQ	see Figure 6				
		V_{CC} = 2.0 V	-	33	110	ns
		V_{CC} = 4.5 V	-	12	22	ns
		V_{CC} = 6.0 V	-	10	19	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	11	-	ns
	propagation delay nD to $n\overline{Q}$	see Figure 7				
		V_{CC} = 2.0 V	-	39	120	ns
		V_{CC} = 4.5 V	-	14	24	ns
		V_{CC} = 6.0 V	-	11	20	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	11	-	ns
	propagation delay LEnn to nQ	see Figure 9				
		V_{CC} = 2.0 V	-	33	120	ns
		V_{CC} = 4.5 V	-	12	24	ns
		V_{CC} = 6.0 V	-	10	20	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	11	-	ns
	propagation delay LEnn to $n\overline{Q}$	see Figure 9				
		V_{CC} = 2.0 V	-	39	125	ns
		V_{CC} = 4.5 V	-	14	25	ns
		V_{CC} = 6.0 V	-	11	21	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	11	-	ns
t_{THL}, t_{TLH}	output transition time	see Figure 6 and 7				
		V_{CC} = 2.0 V	-	19	75	ns
		V_{CC} = 4.5 V	-	7	15	ns
		V_{CC} = 6.0 V	-	6	13	ns
t_W	enable pulse width HIGH	see Figure 9				
		V_{CC} = 2.0 V	80	17	-	ns
		V_{CC} = 4.5 V	16	6	-	ns
		V_{CC} = 6.0 V	14	5	-	ns
t_{su}	set-up time nD to LEnn	see Figure 8				
		V_{CC} = 2.0 V	60	14	-	ns
		V_{CC} = 4.5 V	12	5	-	ns
		V_{CC} = 6.0 V	10	4	-	ns
t_h	hold time nD to LEnn	see Figure 8				
		V_{CC} = 2.0 V	3	–8	-	ns
		V_{CC} = 4.5 V	3	–3	-	ns
		V_{CC} = 6.0 V	3	–2	-	ns

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Table 7. Dynamic characteristics *...continued*

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF; unless otherwise specified, see Figure 10.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{PD}	power dissipation capacitance per latch	V_I = GND to V_{CC} [1]	-	42	-	pF
T_{amb} = –40 °C to +85 °C						
t_{PHL}, t_{PLH}	propagation delay nD to nQ	see Figure 6				
		V_{CC} = 2.0 V	-	-	140	ns
		V_{CC} = 4.5 V	-	-	28	ns
		V_{CC} = 6.0 V	-	-	24	ns
	propagation delay nD to $n\overline{Q}$	see Figure 7				
		V_{CC} = 2.0 V	-	-	150	ns
		V_{CC} = 4.5 V	-	-	30	ns
		V_{CC} = 6.0 V	-	-	26	ns
	propagation delay LEnn to nQ	see Figure 9				
		V_{CC} = 2.0 V	-	-	150	ns
		V_{CC} = 4.5 V	-	-	30	ns
		V_{CC} = 6.0 V	-	-	26	ns
	propagation delay LEnn to $n\overline{Q}$	see Figure 9				
		V_{CC} = 2.0 V	-	-	155	ns
		V_{CC} = 4.5 V	-	-	31	ns
		V_{CC} = 6.0 V	-	-	26	ns
t_{THL}, t_{TLH}	output transition time	see Figure 6 and 7				
		V_{CC} = 2.0 V	-	-	95	ns
		V_{CC} = 4.5 V	-	-	19	ns
		V_{CC} = 6.0 V	-	-	16	ns
t_W	enable pulse width HIGH	see Figure 9				
		V_{CC} = 2.0 V	100	-	-	ns
		V_{CC} = 4.5 V	20	-	-	ns
		V_{CC} = 6.0 V	17	-	-	ns
t_{su}	set-up time nD to LEnn	see Figure 8				
		V_{CC} = 2.0 V	75	-	-	ns
		V_{CC} = 4.5 V	15	-	-	ns
		V_{CC} = 6.0 V	13	-	-	ns
t_h	hold time nD to LEnn	see Figure 8				
		V_{CC} = 2.0 V	3	-	-	ns
		V_{CC} = 4.5 V	3	-	-	ns
		V_{CC} = 6.0 V	3	-	-	ns

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Table 7. Dynamic characteristics *...continued*

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF; unless otherwise specified, see Figure 10.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = –40 °C to +125 °C						
t_{PHL}, t_{PLH}	propagation delay nD to nQ	see Figure 6				
		V_{CC} = 2.0 V	-	-	165	ns
		V_{CC} = 4.5 V	-	-	33	ns
		V_{CC} = 6.0 V	-	-	28	ns
	propagation delay nD to $n\overline{Q}$	see Figure 7				
		V_{CC} = 2.0 V	-	-	180	ns
		V_{CC} = 4.5 V	-	-	36	ns
		V_{CC} = 6.0 V	-	-	31	ns
	propagation delay LEnn to nQ	see Figure 9				
		V_{CC} = 2.0 V	-	-	180	ns
		V_{CC} = 4.5 V	-	-	36	ns
		V_{CC} = 6.0 V	-	-	31	ns
	propagation delay LEnn to $n\overline{Q}$	see Figure 9				
		V_{CC} = 2.0 V	-	-	190	ns
		V_{CC} = 4.5 V	-	-	38	ns
		V_{CC} = 6.0 V	-	-	32	ns
t_{THL}, t_{TLH}	output transition time	see Figure 6 and 7				
		V_{CC} = 2.0 V	-	-	110	ns
		V_{CC} = 4.5 V	-	-	22	ns
		V_{CC} = 6.0 V	-	-	19	ns
t_W	enable pulse width HIGH	see Figure 9				
		V_{CC} = 2.0 V	120	-	-	ns
		V_{CC} = 4.5 V	24	-	-	ns
		V_{CC} = 6.0 V	20	-	-	ns
t_{su}	set-up time nD to LEnn	see Figure 8				
		V_{CC} = 2.0 V	90	-	-	ns
		V_{CC} = 4.5 V	18	-	-	ns
		V_{CC} = 6.0 V	15	-	-	ns
t_h	hold time nD to LEnn	see Figure 8				
		V_{CC} = 2.0 V	3	-	-	ns
		V_{CC} = 4.5 V	3	-	-	ns
		V_{CC} = 6.0 V	3	-	-	ns

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

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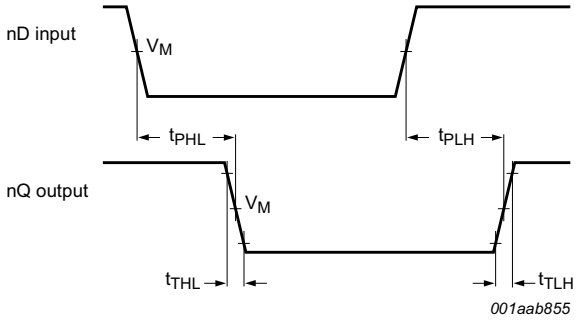
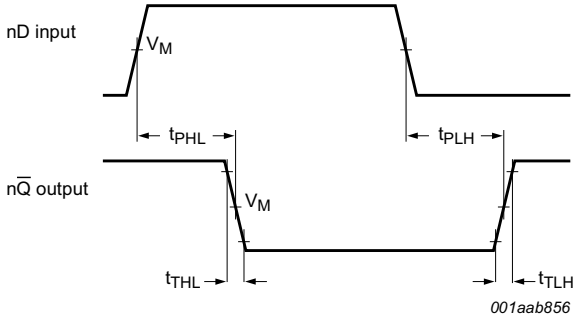
11. Waveforms



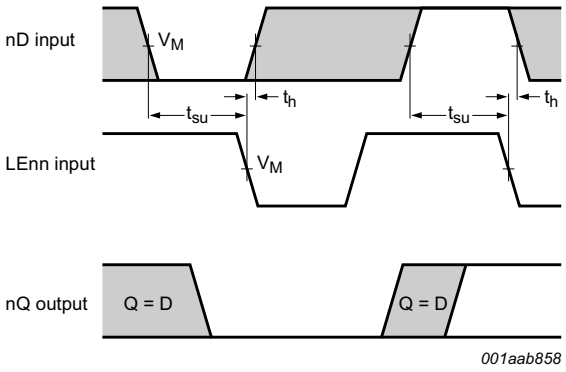
$V_M = 0.5 \times V_I$

Fig 6. Waveforms showing the data input (nD) to output (nQ) propagation delays and the output transition times



$V_M = 0.5 \times V_I$

Fig 7. Waveforms showing the data input (nD) to output ($n\overline{Q}$) propagation delays and the output transition times



The shaded areas indicate when the input is permitted to change for predictable output performance.

$V_M = 0.5 \times V_I$

Fig 8. Waveforms showing the data set-up and hold times for nD input to LEnn input

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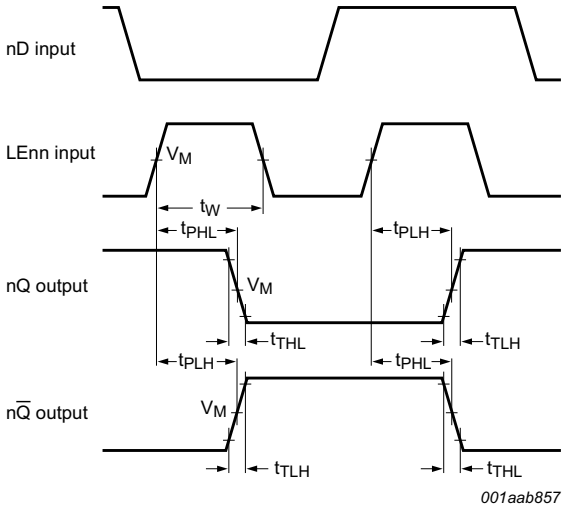
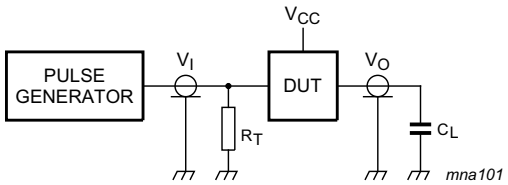


$V_M = 0.5 \times V_I$

Fig 9. Waveforms showing the latch enable input (LEnn) pulse width, the latch enable input to outputs (nQ, n$\overline{Q}$) propagation delays and the output transition times



Test data is given in Table 8

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

Fig 10. Test circuit for measuring switching times

Table 8. Test data

Supply	Input		Load
V_{CC}	V_I	t_r, t_f	C_L
2.0 V	V_{CC}	6 ns	50 pF
4.5 V	V_{CC}	6 ns	50 pF
6.0 V	V_{CC}	6 ns	50 pF
5.0 V	V_{CC}	6 ns	15 pF

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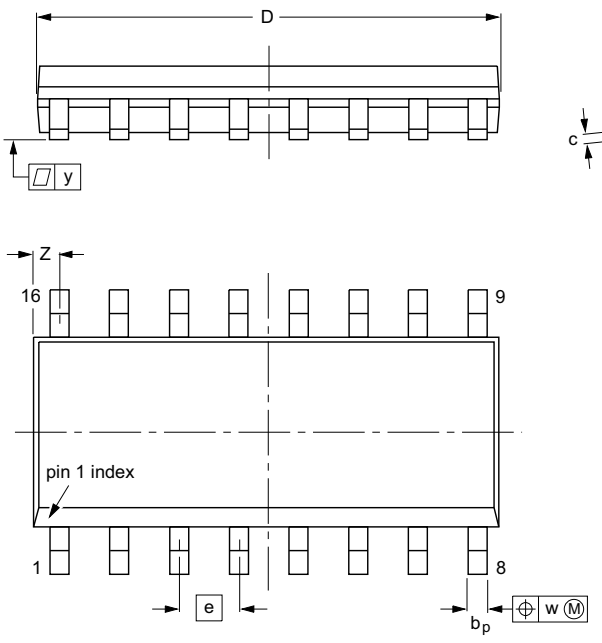
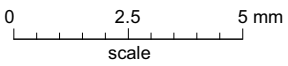
12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**





DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 11. Package outline SOT109-1 (SO16)

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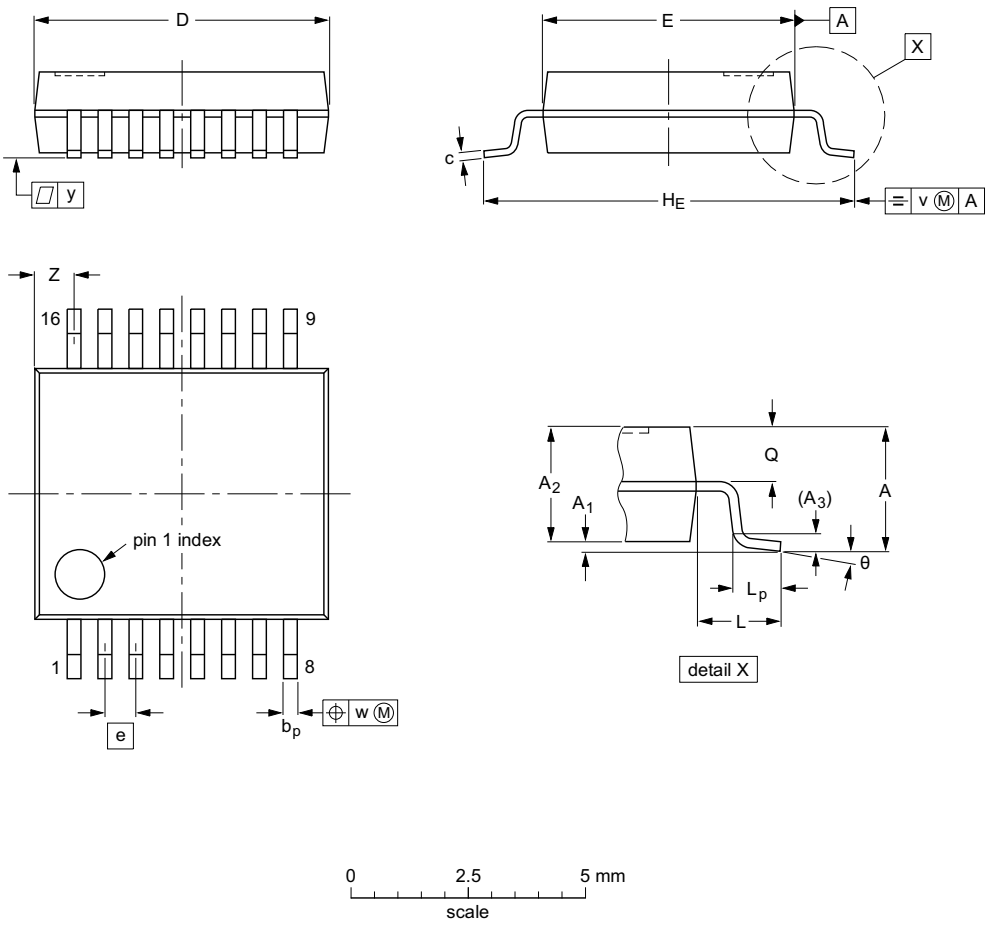
SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 12. Package outline SOT338-1 (SSOP16)

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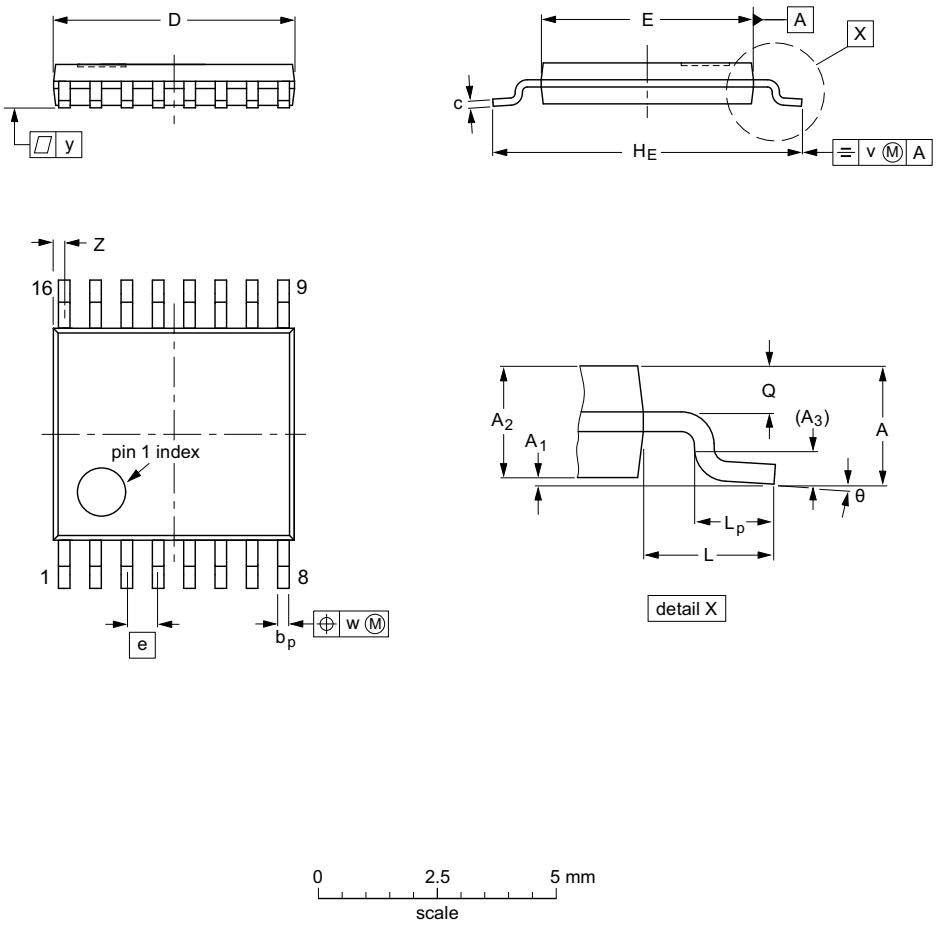
TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 13. Package outline SOT403-1 (TSSOP16)

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13. Abbreviations

Table 9. Abbreviations

Acronym	Abbreviation
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC75 v.4	20160224	Product data sheet	-	74HC75 v.3
Modifications:	• Type number 74HC75N (SOT38-4) removed.			
74HC75 v.3	20041112	Product data sheet	-	74HC_HCT75_CNV v.2
Modifications:	• The format of this data sheet has been redesigned to comply with the current presentation and information standard of Philips Semiconductors. • Removed type number 74HCT75. • Inserted family specification.			
74HC_HCT75_CNV v.2	19970918	Product specification	-	74HC_HCT75 v.1
74HC_HCT75 v.1	19901201	Product specification	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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